

3SK272

GaAs N-Channel MES

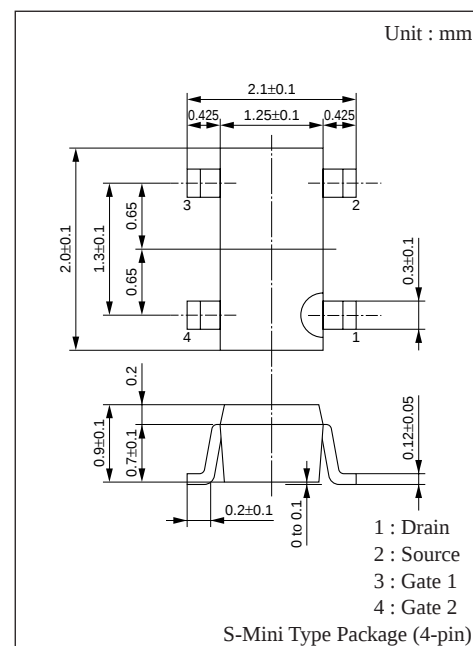
For VHF-UHF amplification

■ Features

- Low noise-figure (NF)
- Large power gain PG
- Downsizing of sets by S-mini power package and automatic insertion by taping/magazine packing are available.

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	13	V
Gate 1-Source voltage	V_{G1S}	− 6	V
Gate 2-Source voltage	V_{G2S}	− 6	V
Drain current	I_D	50	mA
Gate 1 current	I_{G1}	1	mA
Gate 2 current	I_{G2}	1	mA
Allowable power dissipation	P_D	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	− 55 to +150	°C

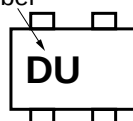


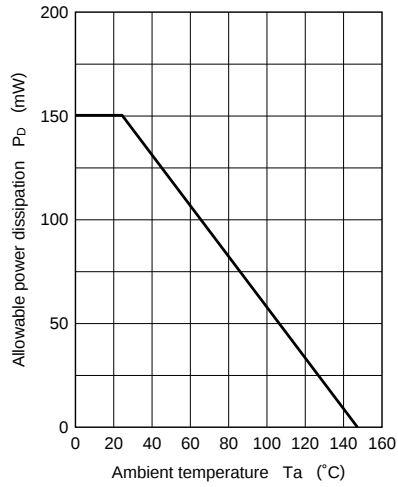
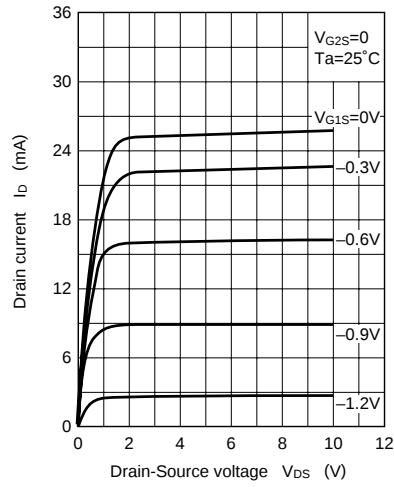
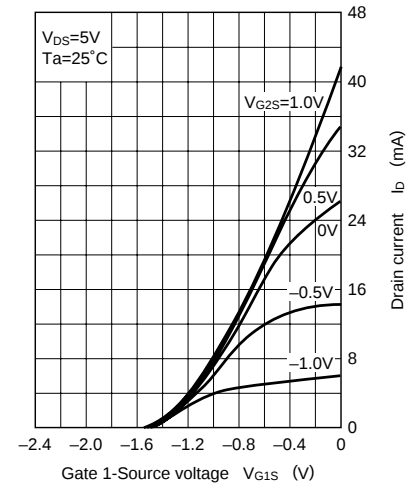
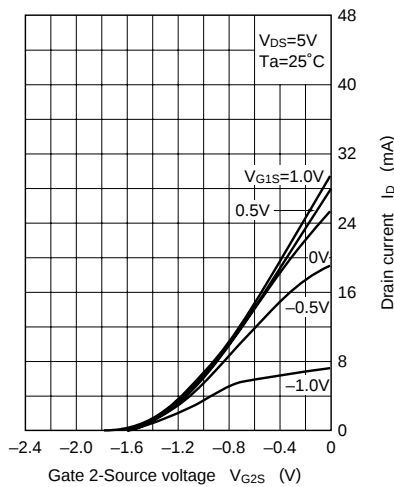
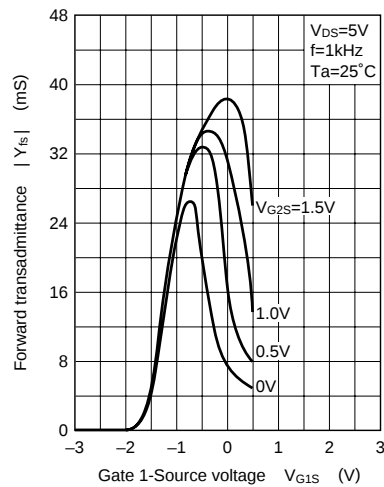
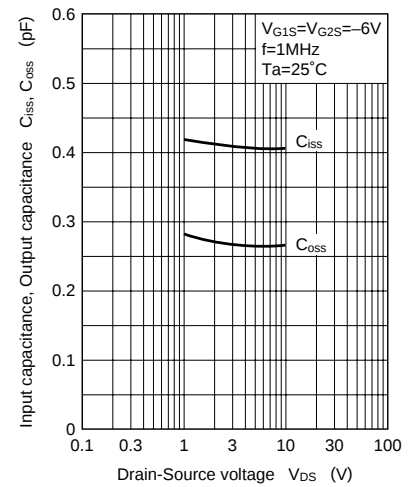
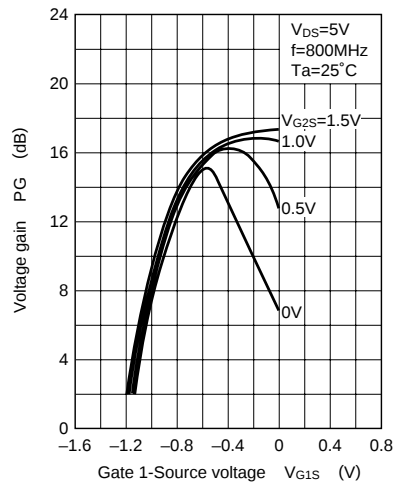
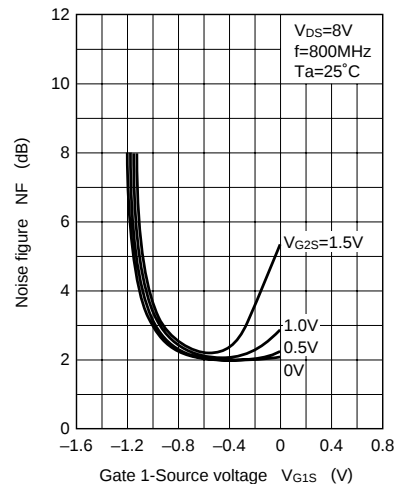
■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	$V_{DS}=5V, V_{G1S}=0, V_{G2S}=0$	8.5		35	mA
Gate 2-Drain current	I_{G2DO}	$V_{G2D}=−13V(G1, S= Open)$			50	μA
Gate 1 cut-off current	I_{G1SS}	$V_{DS}=V_{G2S}=0, V_{G1S}=−6V$			− 20	μA
Gate 2 cut-off current	I_{G2SS}	$V_{DS}=V_{G1S}=0, V_{G2S}=−6V$			− 20	μA
Drain cut-off current	I_{DSX}	$V_{DS}=13V, V_{G1S}=−3.5V, V_{G2S}=0$			50	μA
Gate 1-Source cut-off voltage	V_{G1SC}	$V_{DS}=5V, V_{G2S}=0, I_D=200\mu A$			− 3.5	V
Gate 2-Source cut-off voltage	V_{G2SC}	$V_{DS}=5V, V_{G1S}=0, I_D=200\mu A$			− 3.5	V
Forward transadmittance	$ Y_{fs} $	$V_{DS}=5V, I_D=10mA, V_{G2S}=1.5V, f=1kHz$	18	23		mS
Input capacitance	C_{iss}	$V_{DS}=5V, V_{G1S}=V_{G2S}=−6V, f=1MHz$		0.4	2	pF
Output capacitance	C_{oss}			0.3	1.2	pF
Feedback capacitance	C_{rss}			0.02	0.04	pF
Power gain	PG	$V_{DS}=5V, I_D=10mA,$	10	16		dB
Noise figure	NF	$V_{G2S}=1.5V, f=800MHz$		1.8	2.8	dB
Gain reduction	G_R	$V_{DS}=5V, V_{AGC}=1.5V/-3.5V, f=800MHz$	37	45		dB

■ Marking

Part Number



$P_D - T_a$  $I_D - V_{DS}$  $I_D - V_{G1S}$  $I_D - V_{G2S}$  $|Y_{fs}| - V_{G1S}$  $C_{iss}, C_{oss} - V_{DS}$  $PG - V_{G1S}$  $NF - V_{G1S}$  $PG - V_{G2S}$ 